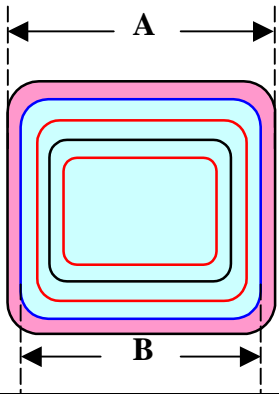


| | | | | |
|--|--------------------|------------------------------|-------|--|
| Features : <ul style="list-style-type: none"> * Extremely low forward volts * Guard ring protection * Low reverse leakage current  | Chip size(A): | 2.210* 2.210 mm ² | | |
| | Bond Pad size(B) : | 2.083 *2.083 mm ² | | |
| | Thickness : | 300μm ± 20μm | | |
| | Metalization : | Anode Ti/Ni/Ag | | |
| | Metalization : | Cathode Ti/Ni/Ag | | |
| Electrical Characteristics | Sym. | Spec. Limit | Unit | |
| Maximum Instantaneous Forward Volt at IF : 8.0Amp. 25°C | VF max | 0.73 | Volt | |
| Minimum Instantaneous Reverse Voltage at IR : 300 uA 25°C | VR min. | 63 | Volt. | |
| Minimum Non-repetitive Peak Surge current at 25°C | IFSM | 150 | Amp | |
| Storage Temperature | TSTG | -65 to +125 | °C | |

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